

**SEMICONDUCTOR DEVICE HAVING SELF-ALIGNED CONTACT  
AND FABRICATING METHOD THEREFOR**

**Abstract of the Disclosure**

A semiconductor device having a self-aligned contact and a method for  
5 fabricating the same are provided. The semiconductor device includes a plurality of  
conductive patterns formed to be adjacent to one another by sequentially stacking and  
patterning a first conductive layer and a mask layer on a particular underlying layer. A  
first insulation layer fills a gap between adjacent conductive layer patterns such that the  
upper portion of each conductive layer pattern is exposed. A second insulation layer  
10 having a spacer shape is formed on the sides of each conductive layer pattern exposed  
above the first insulation layer. A second conductive layer fills a contact hole which is  
self-aligned with respect to the second insulation layers between adjacent conductive  
layer patterns and passes through the first insulation layer.

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